

Important notice

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Kind regards,

Team Nexperia

74ABT544

Octal latched transceiver with dual enable; 3-state

Rev. 6 — 3 November 2011

Product data sheet

1. General description

The 74ABT544 high performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT544 octal latched transceiver contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch enable (LEAB, LEBA) and output enable (OEAB, OEBA) inputs are provided for each register to permit independent control of data transfer in either direction. The outputs are guaranteed to sink 64 mA.

2. Features and benefits

- Combines 74ABT640 and 74ABT373 type functions in one device
- 8-bit octal transceiver with D-type latch
- Back-to-back registers for storage
- Separate controls for data flow in each direction
- Live insertion and extraction permitted
- Output capability: +64 mA to -32 mA
- Power-up 3-state
- Power-up reset
- Latch-up protection exceeds 500 mA per JESD78B class II level A
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V

3. Ordering information

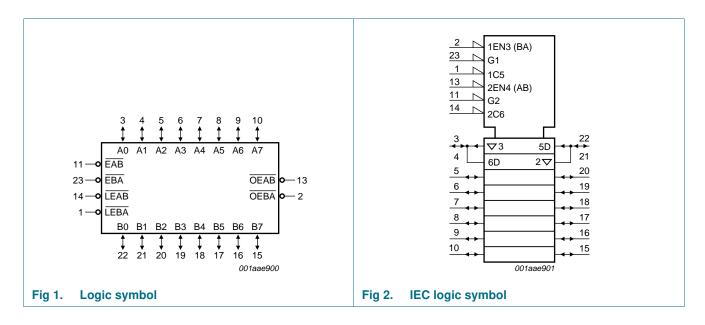
Table 1. Ordering information

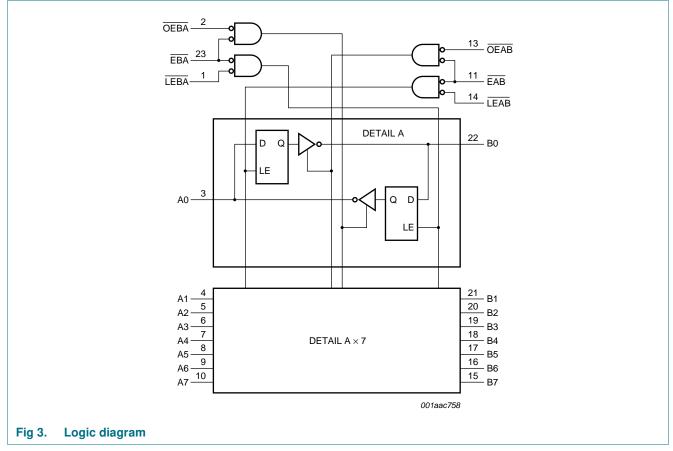
Type number	Package	Package										
	Temperature range	Name	Description	Version								
74ABT544D	–40 °C to +85 °C	SO24	plastic small outline package; 24 leads; body width 7.5 mm	SOT137-1								
74ABT544DB	–40 °C to +85 °C	SSOP24	plastic shrink small outline package; 24 leads; body width 5.3 mm	SOT340-1								
74ABT544PW	–40 °C to +85 °C	TSSOP24	plastic thin shrink small outline package; 24 leads; body width 4.4 mm	SOT355-1								



Octal latched transceiver with dual enable; 3-state

4. Functional diagram

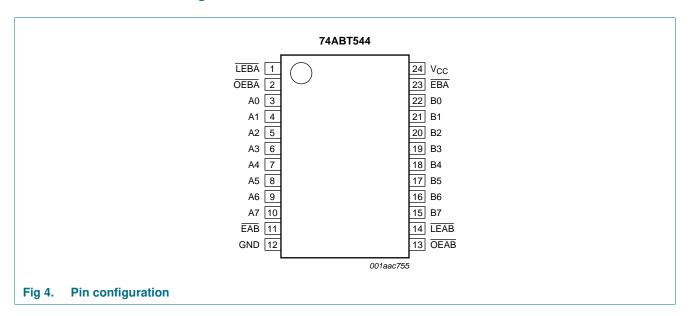




Octal latched transceiver with dual enable; 3-state

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
LEBA	1	B-to-A latch enable input (active LOW)
OEBA	2	B-to-A output enable input (active LOW)
A0 to A7	3, 4, 5, 6, 7, 8, 9, 10	data input or output
EAB	11	A-to-B enable input (active LOW)
GND	12	ground (0 V)
OEAB	13	A-to-B output enable input (active LOW)
LEAB	14	A-to-B latch enable input (active LOW)
B0 to B7	22, 21, 20, 19, 18, 17, 16, 15	data input or output
EBA	23	B-to-A enable input (active LOW)
V _{CC}	24	positive supply voltage

Octal latched transceiver with dual enable: 3-state

6. Functional description

6.1 Function table

Table 3. Function selection[1]

Input				Output	Status
OEXX	EXX	LEXX	An or Bn	Bn or An	
Н	X	X	X	Z	disabled
Χ	Н	Χ	Χ	Z	
L	↑	L	h	Z	disabled + latch
			I	Z	
L	L	↑	h	L	latch + display
			I	Н	
L	L	L	Н	L	transparent
			L	Н	
L	L	Н	Χ	NC	hold

^[1] H = HIGH voltage level;

NC = no change;

X = don't care;

6.2 Description

The 74ABT544 contains two sets of eight D-type latches, with separate control pins for each set.

Using data flow from A-to-B as an example, when the A-to-B enable $(\overline{\sf EAB})$ input, the A-to-B latch enable $(\overline{\sf LEAB})$ input and the A-to-B output enable $(\overline{\sf OEAB})$ input are all LOW, the A-to-B path is transparent.

A subsequent LOW-to-HIGH transition of the LEAB signal puts the A data into the latches where it is stored and the B outputs no longer change with the A inputs. With EAB and OEAB both LOW, the 3-state B output buffers are active and display the data present at the outputs of the A latches.

Control of data flow from B-to-A is similar, but using the EBA, LEBA, and OEBA inputs.

 $h = HIGH \text{ voltage level one set-up time prior to the LOW-to-HIGH clock transition of } \overline{LEXX} \text{ or } \overline{EXX} \text{ (XX = AB or BA);}$

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition of LEXX or EXX (XX = AB or BA);

 $[\]uparrow$ = LOW-to-HIGH clock transition of \overline{LEXX} or \overline{EXX} (XX = AB or BA);

Z = high-impedance OFF-state.

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		<u>[1]</u> –1.2	+7.0	V
V _O	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+5.5	V
I _{IK}	input clamping current	V _I < 0 V	-18	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Io	output current	output in LOW-state	-	128	mA
Tj	junction temperature		[2] _	150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		4.5	-	5.5	V
VI	input voltage		0	-	V_{CC}	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current		-	-	64	mA
$\Delta t/\Delta V$	input transition rise and fall rate		0	-	10	ns/V
T _{amb}	ambient temperature	in free air	-40	-	+85	°C

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C to	+85 °C	Unit
				Тур	Max	Min	Max	
V_{IK}	input clamping voltage	$V_{CC} = 4.5 \text{ V}; I_{IK} = -18 \text{ mA}$	-1.2	-0.9	-	-1.2	-	V
V _{OH} HIGH-level output		$V_I = V_{IL} \text{ or } V_{IH}$						
	voltage	$V_{CC} = 4.5 \text{ V}; I_{OH} = -3 \text{ mA}$	2.5	3.2	-	2.5	-	V
		$V_{CC} = 5.0 \text{ V}; I_{OH} = -3 \text{ mA}$	3.0	3.7	-	3.0	-	V
		$V_{CC} = 4.5 \text{ V}; I_{OH} = -32 \text{ mA}$	2.0	2.3	-	2.0	-	٧
V_{OL}	LOW-level output voltage	V_{CC} = 4.5 V; I_{OL} = 64 mA; V_I = V_{IL} or V_{IH}	-	0.42	0.55	-	0.55	V

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^[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

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Table 6. Static characteristics ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			25 °C		–40 °C t	o +85 °C	Unit
				Min	Тур	Max	Min	Max	
$V_{OL(pu)}$	power-up LOW-level output voltage	V_{CC} = 5.5 V; I_{O} = 1 mA; V_{I} = GND or V_{CC}	[1]	-	0.13	0.55	-	0.55	V
l _l	input leakage current	$V_{CC} = 5.5 \text{ V}; V_I = \text{GND or } 5.5 \text{ V}$							
		control pins		-	±0.01	±1.0	-	±1.0	μΑ
		An, Bn		-	±5.0	±100	-	±100	μА
I _{OFF}	power-off leakage current	V_{CC} = 0 V; V_{I} or $V_{O} \le 4.5$ V		-	±5.0	±100	-	±100	μΑ
$I_{O(pu/pd)}$	power-up/power-down output current	V_{CC} = 2.1 V; V_{O} = 0.5 V; V_{I} = GND or V_{CC} ; OEAB, OEBA don't care	[2]	-	±5.0	±50	-	±50	μΑ
l _{OZ}	OFF-state output	$V_{CC} = 5.5 \text{ V}; V_I = V_{IL} \text{ or } V_{IH}$							
	current	$V_0 = 2.7 \text{ V}$		-	5.0	50	-	50	μΑ
		$V_{O} = 0.5 \text{ V}$		-	-5.0	-50	-	-50	μΑ
I_{LO}	output leakage current	HIGH-state; $V_O = 5.5 \text{ V}$; $V_{CC} = 5.5 \text{ V}$; $V_I = \text{GND or } V_{CC}$		-	5.0	50	-	50	μΑ
Io	output current	$V_{CC} = 5.5 \text{ V}; V_O = 2.5 \text{ V}$	[3]	-180	-65	-50	-180	-50	mΑ
I _{CC}	supply current	V_{CC} = 5.5 V; V_I = GND or V_{CC}							
		outputs HIGH-state		-	110	250	-	250	μΑ
		outputs LOW-state		-	20	30	-	30	mA
		outputs disabled		-	110	250	-	250	μΑ
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 5.5 V; one input pin at 3.4 V, other inputs at V_{CC} or GND	[4]	-	0.3	1.5	-	1.5	mA
Cı	input capacitance	$V_I = 0 \text{ V or } V_{CC}$		-	4	-	-	-	рF
C _{I/O}	input/output capacitance	outputs disabled; $V_O = 0 V \text{ or } V_{CC}$		-	7	-	-	-	pF

^[1] For valid test results, data must not be loaded into the flip-flops (or latches) after applying the power.

10. Dynamic characteristics

Table 7. Dynamic characteristics GND = 0 *V; for test circuit, see Figure 10.*

Symbol	Parameter	Conditions	25 °C	; V _{CC} =		-40 °C to V _{CC} = 5.0		
			Min	Тур	Max	Min	Max	
t _{PLH}	LOW to HIGH	An to Bn or Bn to An; see Figure 5	1.7	3.0	3.8	1.7	4.7	ns
	propagation delay	LEBA to An or LEAB to Bn; see Figure 6	2.1	3.5	4.2	2.1	5.2	ns

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^[2] This parameter is valid for any V_{CC} between 0 V and 2.1 V, with a transition time of up to 10 ms. From V_{CC} = 2.1 V to V_{CC} = 5 V \pm 10 %, a transition time of up to 100 μ s is permitted.

^[3] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

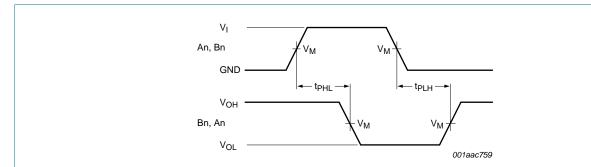
^[4] This is the increase in supply current for each input at 3.4 V.

Octal latched transceiver with dual enable; 3-state

Table 7. Dynamic characteristics ...continued GND = 0 V; for test circuit, see <u>Figure 10</u>.

Symbol	Parameter	Conditions		; V _{CC} =	5.0 V	-40 °C to V _{CC} = 5.0	+85 °C; V ± 0.5 V	Unit
			Min	Тур	Max	Min	Max	
t _{PHL}	HIGH to LOW	An to Bn or Bn to An; see Figure 5	2.4	3.6	4.5	2.4	5.2	ns
	propagation delay	LEBA to An or LEAB to Bn; see Figure 6	3.0	4.4	5.3	3.0	6.2	ns
t_{PZH}	OFF-state to HIGH	OEBA to An, OEAB to Bn; see Figure 7	1.8	3.0	3.9	1.8	4.7	ns
	propagation delay	EBA to An, EAB to Bn; see Figure 7	1.9	3.4	4.1	1.9	5.0	ns
t _{PZL}	OFF-state to LOW	OEBA to An, OEAB to Bn; see Figure 8	2.9	4.2	5.2	2.9	6.1	ns
	propagation delay	EBA to An, EAB to Bn; see Figure 8	3.1	4.6	5.5	3.1	6.5	ns
t _{PHZ}	HIGH to OFF-state	OEBA to An, OEAB to Bn; see Figure 7	2.0	3.3	4.3	2.0	4.9	ns
	propagation delay	EBA to An, EAB to Bn; see Figure 7	2.1	3.4	4.5	2.1	5.2	ns
t _{PLZ}	LOW to OFF-state	OEBA to An, OEAB to Bn; see Figure 8	2.0	2.8	5.8	2.0	6.3	ns
	propagation delay	EBA to An, EAB to Bn; see Figure 8	2.0	3.0	6.2	2.0	6.7	ns
$t_{\text{su}(H)}$	set-up time HIGH	An to LEAB, Bn to LEBA; see Figure 9	3.0	1.5	-	3.0	-	ns
		An to EAB, Bn to EBA; see Figure 9	3.0	1.5	-	3.0	-	ns
$t_{su(L)}$	set-up time LOW	An to LEAB, Bn to LEBA; see Figure 9	3.0	0.6	-	3.0	-	ns
		An to EAB, Bn to EBA; see Figure 9	3.0	0.6	-	3.0	-	ns
t _{h(H)}	hold time HIGH	LEAB to An, LEBA to Bn; see Figure 9	+0.5	-0.3	-	0.5	-	ns
		EAB to An, EBA to Bn; see Figure 9	+0.5	-0.2	-	0.5	-	ns
t _{h(L)}	hold time LOW	LEAB to An, LEBA to Bn; see Figure 9	+0.5	-1.3	-	0.5	-	ns
		EAB to An, EBA to Bn; see Figure 9	+0.5	-1.3	-	0.5	-	ns
t _{WL}	pulse width LOW	latch enable; see Figure 9	3.5	1.8	-	3.5	-	ns

11. Waveforms

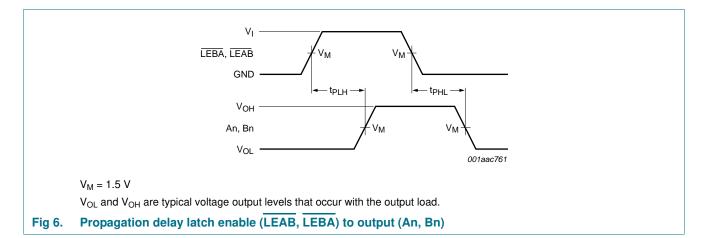


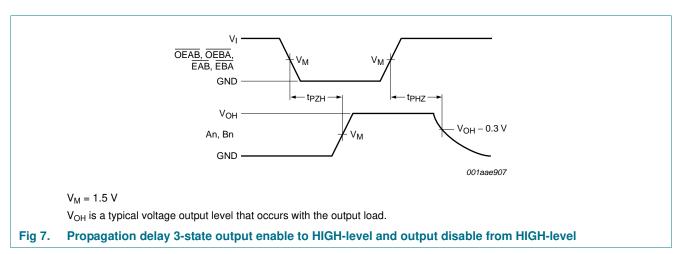
 $V_M = 1.5 V$

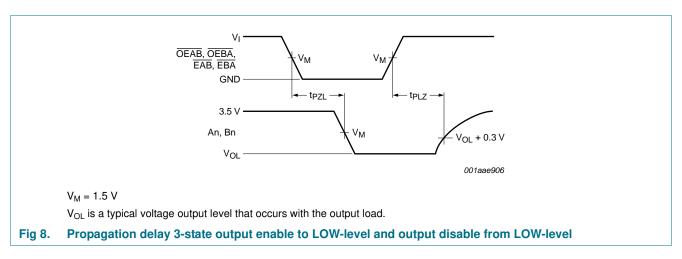
 $\ensuremath{V_{\text{OL}}}$ and $\ensuremath{V_{\text{OH}}}$ are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (An, Bn) to output (Bn, An)

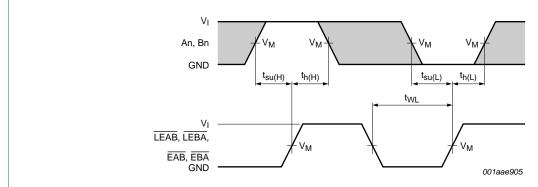
Octal latched transceiver with dual enable; 3-state







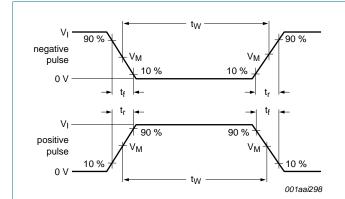
Octal latched transceiver with dual enable; 3-state

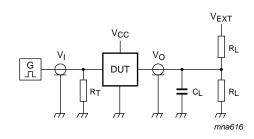


 $V_{M} = 1.5 V$

The shaded areas indicate when the input is permitted to change for predictable output performance.

Fig 9. Data set-up and hold times and latch enable pulse width





b. Test circuit

a. Input pulse definition

Test data is given in Table 8.

Definitions test circuit:

R_L = Load resistor.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

V_{EXT} = Test voltage for switching times.

Fig 10. Load circuitry for switching times

Table 8. Test data

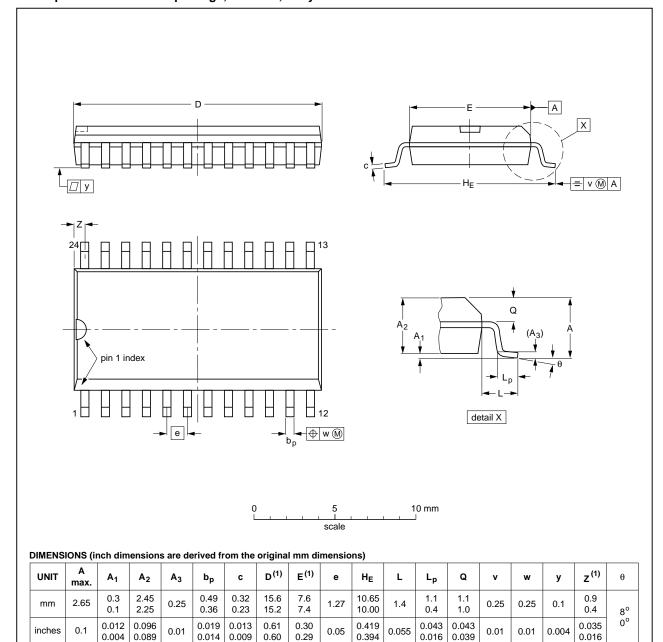
Input	Load		V _{EXT}					
V_{I}	f _I t _W t _r		t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH} t _{PZH} , t _{PHZ}		t _{PZL} , t _{PLZ}
3.0 V	1 MHz	500 ns	\leq 2.5 ns	50 pF	500Ω	open	open	7.0 V

Octal latched transceiver with dual enable; 3-state

12. Package outline

SO24: plastic small outline package; 24 leads; body width 7.5 mm

SOT137-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE	VERSION IEC JEDEC JEITA			EUROPEAN	ISSUE DATE
VERSION	IEC JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT137-1	075E05	MS-013			99-12-27 03-02-19

Fig 11. Package outline SOT137-1 (SO24)

74ABT544

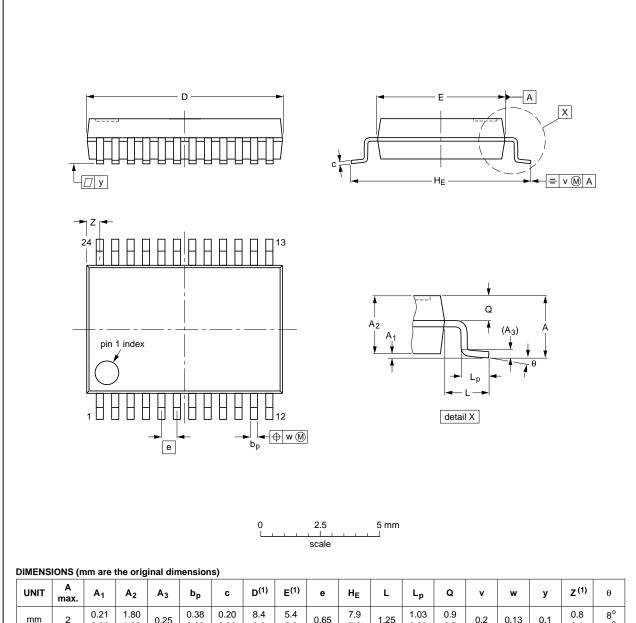
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74ABT544 NXP Semiconductors

Octal latched transceiver with dual enable; 3-state

SSOP24: plastic shrink small outline package; 24 leads; body width 5.3 mm

SOT340-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	٧	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	8.4 8.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.8 0.4	8° 0°

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

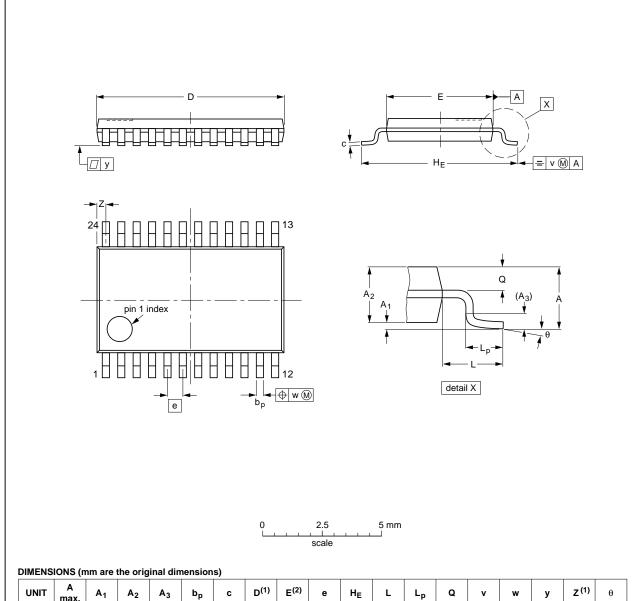
OUTLINE		REFER	EUROPEAN	ICCUIE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT340-1		MO-150				99-12-27 03-02-19

Fig 12. Package outline SOT340-1 (SSOP24)

Octal latched transceiver with dual enable; 3-state

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm

SOT355-1



-							-,												
	UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	7.9 7.7	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT355-1		MO-153				99-12-27 03-02-19

Fig 13. Package outline SOT355-1 (TSSOP24)

74ABT54

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Octal latched transceiver with dual enable; 3-state

13. Abbreviations

Table 9. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

14. Revision history

Table 10. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74ABT544 v.6	20111103	Product data sheet	-	74ABT544 v.5
Modifications:	 Legal pages 	s updated		
74ABT544 v.5	20100520	Product data sheet	-	74ABT544 v.4
74ABT544 v.4	20100115	Product data sheet	-	74ABT544 v.3
74ABT544 v.3	20050420	Product specification	-	74ABT544 v.2
74ABT544 v.2	20021118	Product specification	-	74ABT544
74ABT544	19930701	Product specification	-	-

Octal latched transceiver with dual enable; 3-state

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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